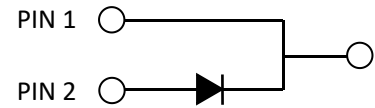


# N0D08065G

## Silicon Carbide Schottky Diode



### Maximum Ratings ( $T_c = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note
$V_{RRM}$	Repetitive Peak Reverse Voltage	650	V		
$V_{RSM}$	Surge Peak Reverse Voltage	650	V		
$V_{DC}$	DC Blocking Voltage	650	V		
$I_F$	Continuous Forward Current	8	A	$T_C=150^\circ\text{C}$	Fig. 7
$I_{FRM}$	Repetitive Peak Forward Surge Current	60	A	$T_C=25^\circ\text{C}$ , $t_p=10$ ms, Half Sine Wave,	
$I_{FSM}$	Non-Repetitive Peak Forward Surge Current	75	A	$T_C=25^\circ\text{C}$ , $t_p=10$ ms, Half Sine Wave	
$I_{F,Max}$	Non-Repetitive Peak Forward Surge Current	680	A	$T_C=25^\circ\text{C}$ , $t_p= 10$ $\mu\text{s}$ , Pulse	
$P_{tot}$	Power Dissipation	136 59	W	$T_C=25^\circ\text{C}$ $T_C=110^\circ\text{C}$	Fig. 6
$T_J, T_{stg}$	Operating Junction and Storage Temperature	-55 to +175	$^\circ\text{C}$		

### Electrical Characteristics

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
$V_F$	Forward Voltage	1.45 1.75	1.70 2.00	V	$I_F = 8$ A $T_J=25^\circ\text{C}$ $I_F = 8$ A $T_J=175^\circ\text{C}$	Fig. 1
$I_R$	Reverse Current	2 40	20 200	$\mu\text{A}$	$V_R = 650$ V $T_J=25^\circ\text{C}$ $V_R = 650$ V $T_J=175^\circ\text{C}$	Fig. 2
$Q_C$	Total Capacitive Charge	22		nC	$V_R = 400$ V, $T_J = 25^\circ\text{C}$ $Q_C = \int_0^{V_R} C(V)dV$	Fig. 4
C	Total Capacitance	440 44 38		pF	$V_R = 0$ V, $T_J = 25^\circ\text{C}$ , $f = 1$ MHz $V_R = 200$ V, $T_J = 25^\circ\text{C}$ , $f = 1$ MHz $V_R = 400$ V, $T_J = 25^\circ\text{C}$ , $f = 1$ MHz	Fig. 3
$E_C$	Capacitance Stored Energy	5.8		$\mu\text{J}$	$V_R = 400$ V	Fig. 5

### Thermal Characteristics

Symbol	Parameter	Typ.	Unit	Note
$R_{\theta JC}$	Thermal Resistance from Junction to Case	1.1	$^\circ\text{C}/\text{W}$	Fig. 8

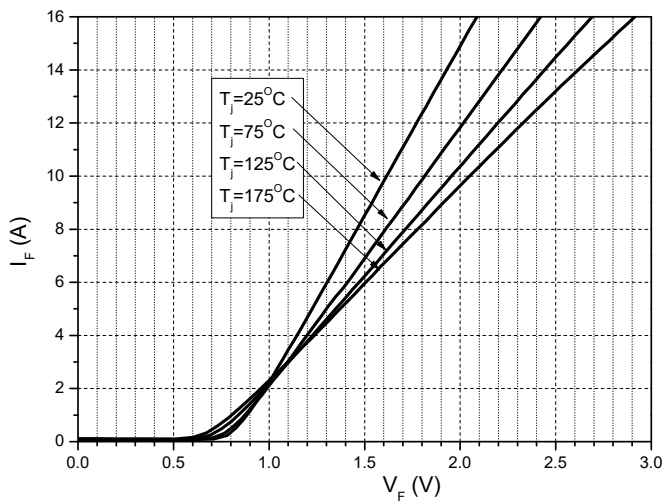


Figure 1. Forward Characteristics

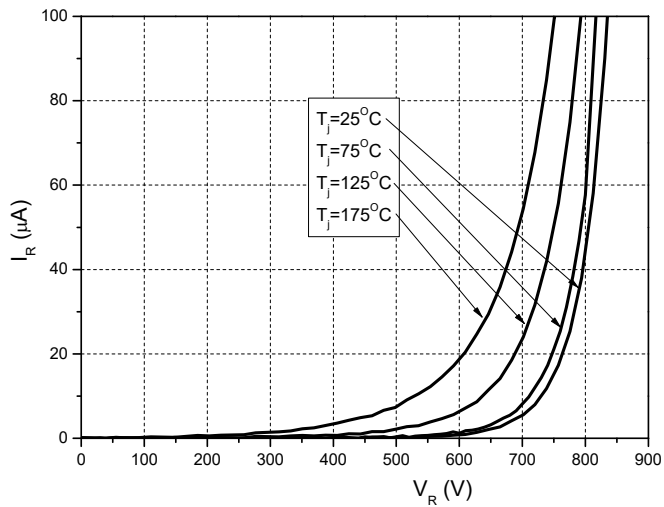


Figure 2. Reverse Characteristics

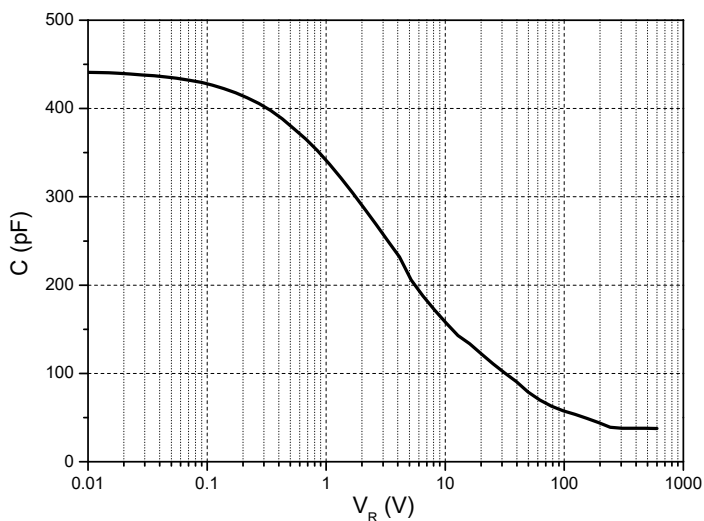


Figure 3. Capacitance vs. Reverse Voltage

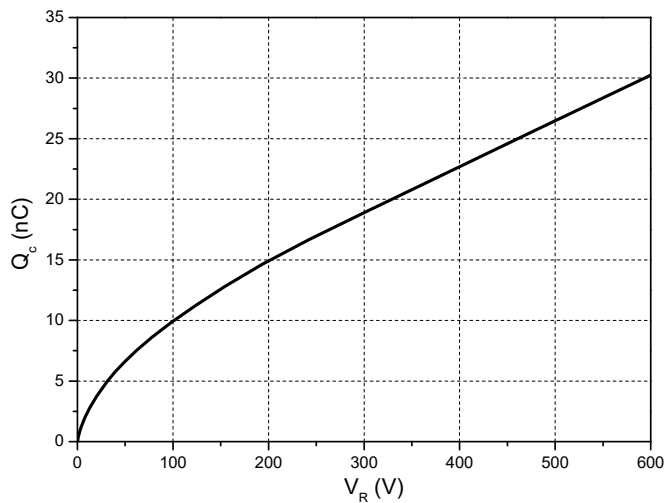


Figure 4. Total Capacitance Charge vs. Reverse Voltage

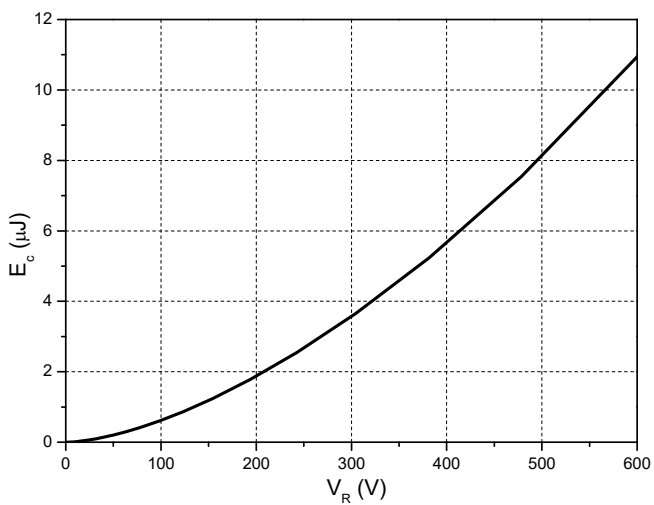


Figure 5. Capacitance Stored Energy

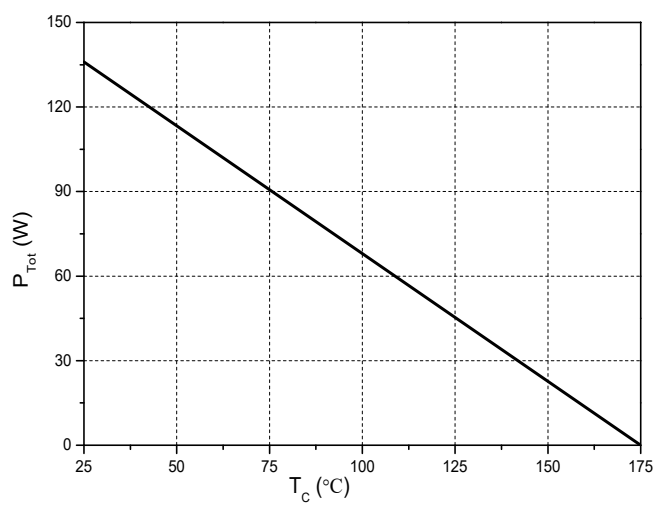


Figure 6. Power Derating

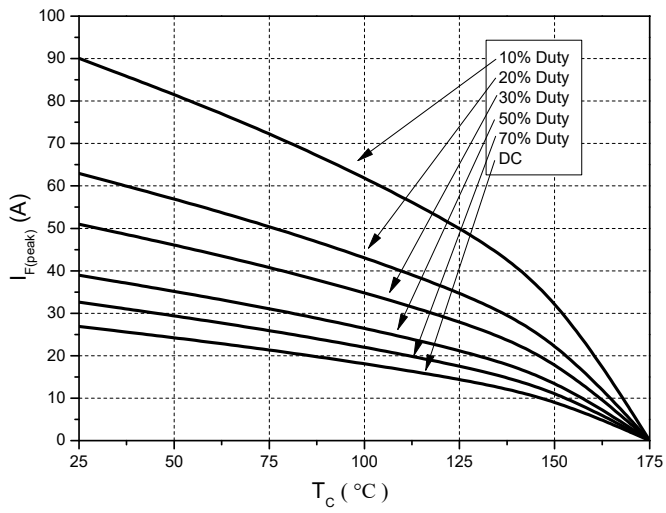


Figure 7. Current Derating

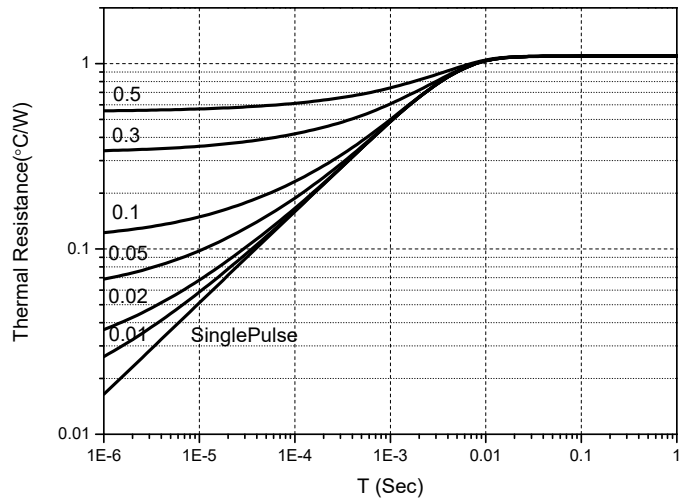
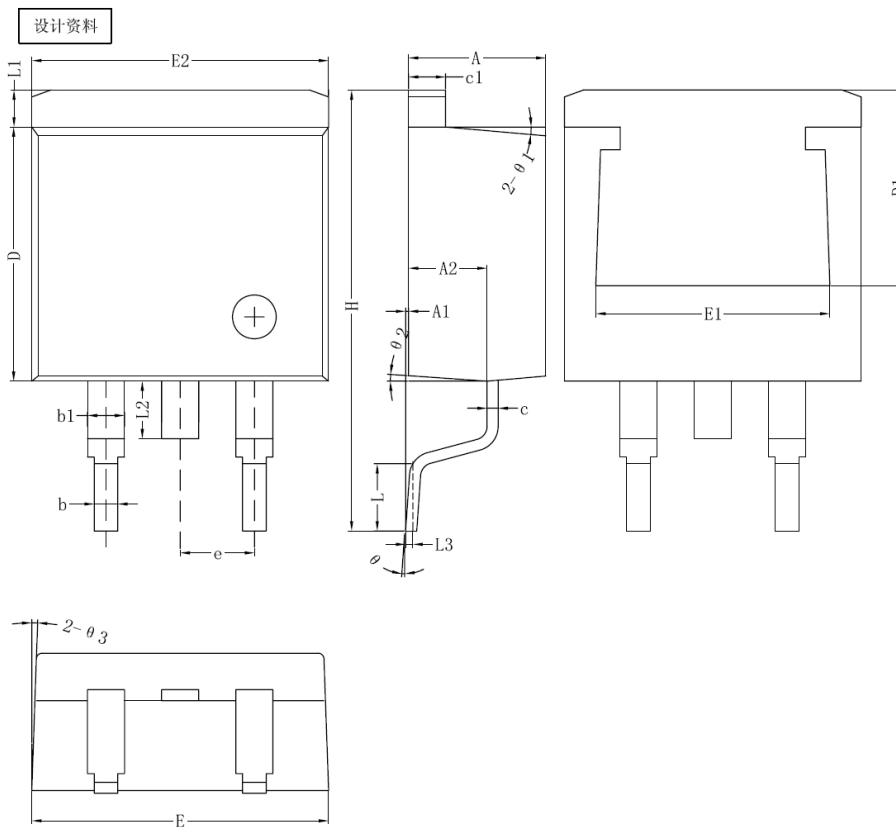


Figure 8. Transient Thermal Impedance

**Package Dimensions : TO263-2L**



符号	机械尺寸/mm		
	最小值	典型值	最大值
A	4.55	4.70	4.85
A1	0	0.10	0.25
A2	2.59	2.69	2.89
b	0.71	0.81	0.96
b1		1.27	
c	0.36	0.38	0.61
c1	1.17	1.27	1.37
D	8.55	8.70	8.85
D1	6.70		7.70
E	10.01	10.16	10.31
E1	7.2		8.1
E2	9.98	10.08	10.18
e		2.54	
H	14.7	15.1	15.5
L	2.00	2.30	2.70
L1	1.17	1.27	1.40
L2			2.20
L3		0.25BSC	
θ	0	-	8°
θ1		5°	
θ2		4°	
θ3		4°	